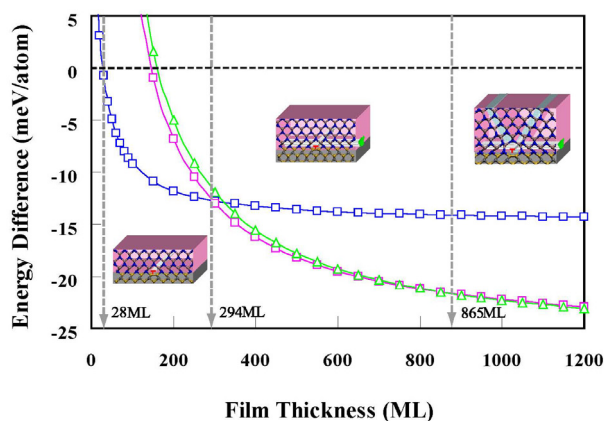
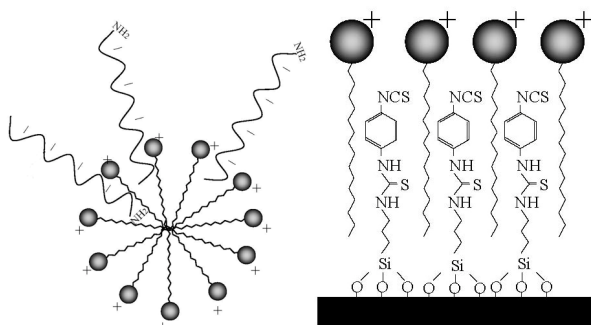


ホームページ : <http://www.sssj.org/ejssnt> 電子メール : ejssnt@sssj.orgJ-Stage アーカイブ : <http://ejssnt.jstage.jst.go.jp>**GaN 薄膜の構造安定性の理論****Theoretical investigation of the structural stability of zinc blende GaN thin films** (Conference –ISSS-4–)

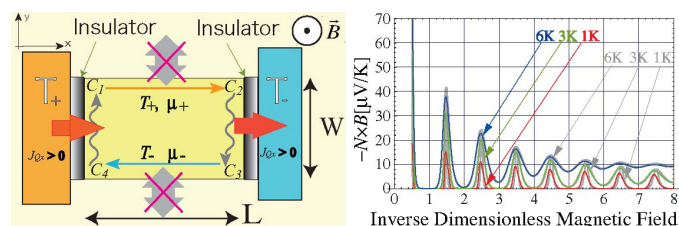
Tatsuya Araki, Toru Akiyama, Kohji Nakamura, and Tomonori Ito, Vol. 3, pp. 507-510 (27 December, 2005)

**共有結合による単鎖DNAの高効率固定化****Highly Efficient and Uniform Single Stranded DNA Immobilization Using a Phase-Transfer Catalyst**

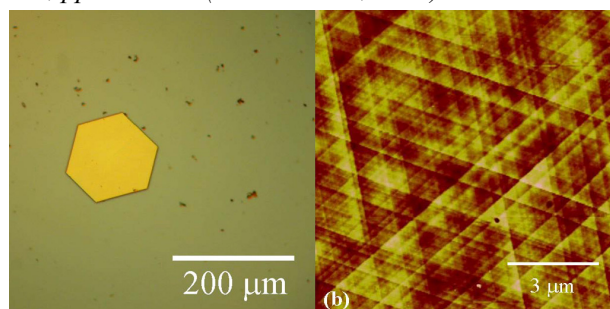
(Conference –ISSS-4–) Miwako Nakahara, Takashi Inoue, Akio Yamane, Toshiaki Ito, Osamu Kogi, and Noriko Ban, Vol. 3, pp. 511-517 (27 December, 2005)

**2次元電子ガス系のNernst効果とSeebeck効果****Impurity Effect in the Quantum Nernst Effect** (Conference –ISSS-4–)

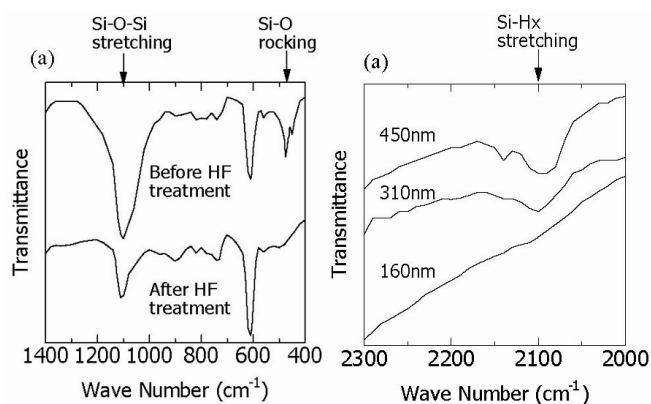
Ryoen Shirasaki, Hiroaki Nakamura, Naomichi Hatano, Vol. 3, pp. 518-523 (27 December, 2005)

**金(111)単結晶プレート作成の新手法****Production method of gold single crystal with high****quality and large grain size and its application to a SPM substrate** (Conference –ISSS-4–)

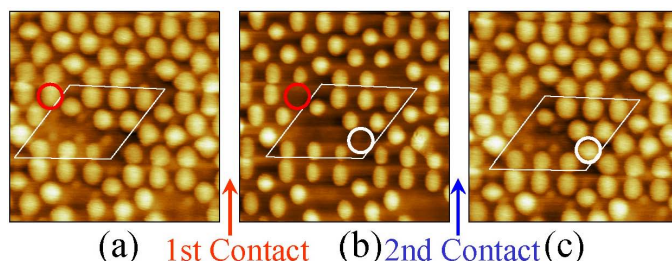
Nobuki Yoshimatsu, Takehiko Kawasaki, Kazuhiro Ban, Takao Kusaka, and Tsutomu Ikeda, Vol. 3, pp. 524-526 (29 December, 2005)

**酸素終端Siナノ結晶を水素終端に置換****H-Termination of Nanocrystalline Si:O Films by HF Solution Treatment** (Conference –ISSS-4–)

Makoto Hirata, Kazuhiro Nakamura, Katsuhiro Yokota, Vol. 3, pp. 527-530 (29 December, 2005)

**AFMによる単一原子操作****Mechanical Atom Manipulation and Artificial Nanostructuring at Low Temperature**

(Conference –ISSS-4–) Noriaki Oyabu, Oscar Custance, Masayuki Abe, and Seizo Morita, Vol. 4, pp. 1-8 (12 January, 2006)

**生化学輸送のラベルとしてのコロイドナノ粒子**
Designing Plasmonic Nanomaterials as Sensors of

Alexander Wei,

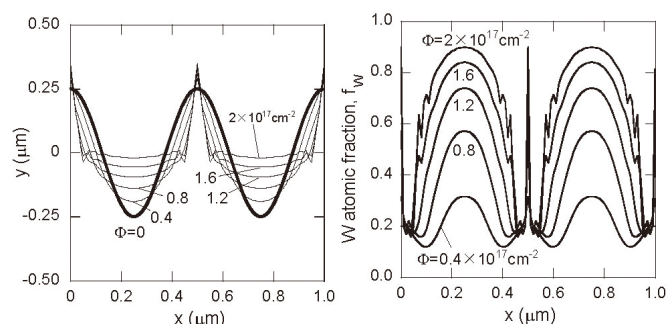
**Growth Simulation and Actual MBE Growth of
Triangular GaAs Nanowires on Patterned (111)B
Substrates** (Conference –ISSS-4-)

Strain distribution due to ion implantation revealed by extremely asymmetric x-ray diffraction
(Conference –ISSS-4-)

Figure 1 consists of two panels. Panel (a) is a plot of X-ray diffraction (XRD) patterns. The x-axis is labeled 'Deviation from bulk peak (arc seconds)' and ranges from -500 to 200. The y-axis is labeled 'Intensity (arb. units)'. Two data series are shown: 'wavelength 0.1623 nm' (blue circles) and 'calculated' (red line). Both series show a series of oscillations with a sharp peak at 0 arc seconds. Panel (b) is a high-resolution transmission electron microscopy (HRTEM) image showing a lattice of atoms. A scale bar in the bottom right corner indicates 1 nm. The text 'Al surface' is written in the top right corner.

Dynamic Monte Carlo Simulation of Compositional and Topography Changes Induced by Ion Beam Irradiation
(Conference –ISSS-4-) *Kensuke Inai and Kaoru Ohya,*

Vol. 4, pp. 32-38 (12 January, 2005)



Adsorption behavior of (CH₃)₂S on sputtered and annealed Rh(100) surface by AFM, XPS and NEXAFS
(Conference -ISSS-4-)

A New Type of Adsorbent Based on the Immobilization of Humic Acid on Chitin and Its Application to Adsorb Cu(II) (Conference –ISSS-4-)

Transmission

3000 2000 1500 1000 500 cm^{-1}

$\nu(\text{O-H})$ of COOH from HA
 2900
 $\nu(\text{C-H})$ of CH_3
 $\nu(\text{C-O})$, $\delta(\text{N-H})$
 $\nu(\text{N-H})$
 $\nu(\text{C-O})$
 $\delta_{\text{as}}(\text{C-CH}_3)$, $\delta_{\text{s}}(\text{C-CH}_3)$
 $\nu(\text{C-Cl})$
 $\nu(\text{N-C})$
 $\nu(\text{C-Cl})$

Surface-phase equilibria in MBE of strained In_{1-x}Ga_xAs heteroepitaxial layers
(Conference –ISSS-4-)